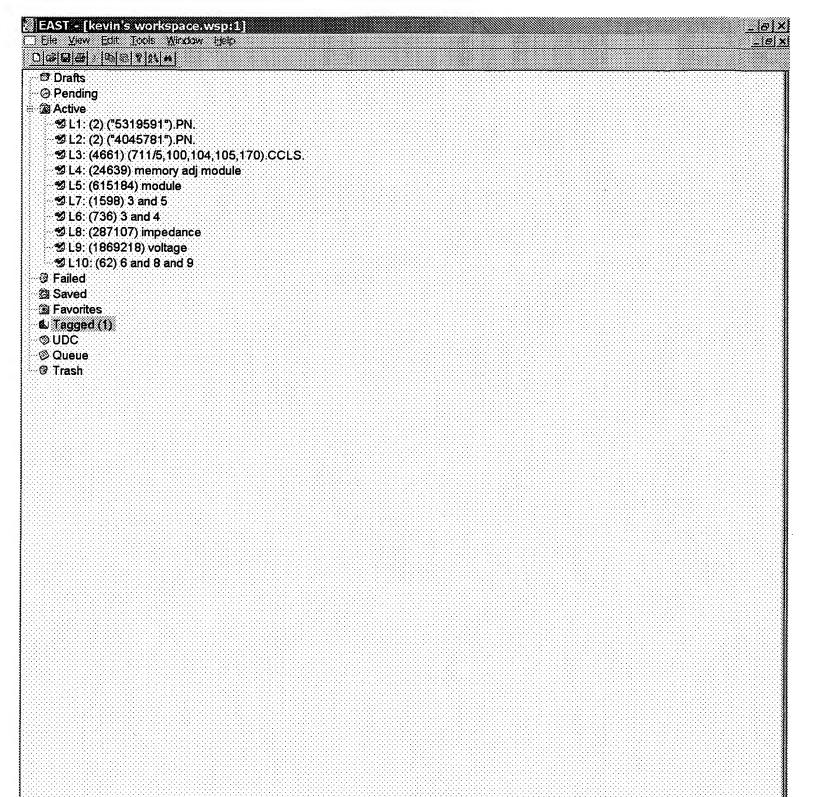
Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	("5319591").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/20 09:41
L2	2	("4045781").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/20 09:45
L3	4661	(711/5,100,104,105,170).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/20 11:16
L4	24639	memory adj module	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 11:16
L5	615184	module	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 11:16
L6	736	3 and 4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 11:17
L7	1598	3 and 5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 11:16
L8	287107	impedance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 11:17
L9	1869218	voltage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/20 11:17

L10	62	6 and 8 and 9	US-PGPUB;	OR	ON	2005/05/20 11:17
			USPAT;			
	1		EPO; JPO;			
	1		DERWENT;			
			IBM_TDB			



	U	•	Document ID a	Issue Date Pages	Inventor	Title	Current OR Cu
1	Г	P	US 5802395 A	19980901 9	Connolly; Brian J. et al.	High density memory modules	710/14 365
						with improved data but performs	710
<u>*1</u>				***************************************			2
# BRS to	180   44	ı ISU	Riffers (*) Details				